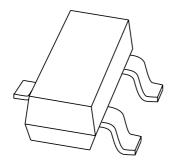
DISCRETE SEMICONDUCTORS

DATA SHEET



BAV199 Low-leakage double diode

Product specification Supersedes data of 1999 May 11 2001 Oct 12





Low-leakage double diode

BAV199

FEATURES

- Plastic SMD package
- · Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

 Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are connected in series.

MARKING

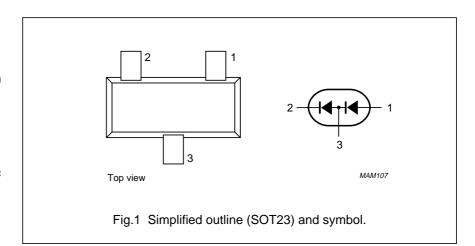
| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|--------------------------------|
| BAV199 | JY* |

Note

1. * = p: Made in Hong Kong.* = t: Made in Malaysia.* = W: Made in China.

PINNING

| PIN | DESCRIPTION |
|-----|----------------|
| 1 | anode |
| 2 | cathode |
| 3 | anode; cathode |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | PARAMETER CONDITIONS | | MAX. | UNIT |
|------------------|-------------------------------------|---|-----|------|------|
| Per diode | | | • | • | • |
| V_{RRM} | repetitive peak reverse voltage | | _ | 85 | V |
| V_R | continuous reverse voltage | | _ | 75 | V |
| I _F | continuous forward current | single diode loaded; note 1; see Fig.2 | _ | 160 | mA |
| | | double diode loaded; note 1; see Fig.2 | _ | 140 | mA |
| I _{FRM} | repetitive peak forward current | | _ | 500 | mA |
| I _{FSM} | non-repetitive peak forward current | square wave; T _j = 25 °C prior to surge; see Fig.4 | | | |
| | | $t_p = 1 \mu s$ | _ | 4 | Α |
| | | $t_p = 1 \text{ ms}$ | _ | 1 | Α |
| | | t _p = 1 s | _ | 0.5 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C; note 1 | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |

Note

1. Device mounted on a FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|-----------------|-----------------------|--|-------|------|------|
| Per diode | | | | • | |
| V _F | forward voltage | see Fig.3 | | | |
| | | I _F = 1 mA | _ | 900 | mV |
| | | I _F = 10 mA | _ | 1000 | mV |
| | | I _F = 50 mA | _ | 1100 | mV |
| | | I _F = 150 mA | _ | 1250 | mV |
| I _R | reverse current | see Fig.5 | | | |
| | | V _R = 75 V | 0.003 | 5 | nA |
| | | V _R = 75 V; T _j = 150 °C | 3 | 80 | nA |
| C _d | diode capacitance | f = 1 MHz; V _R = 0; see Fig.6 | 2 | _ | pF |
| t _{rr} | reverse recovery time | when switched from $I_F = 10$ mA to | 0.8 | 3 | μs |
| | | I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7 | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R _{th j-tp} | thermal resistance from junction to tie-point | | 360 | K/W |
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

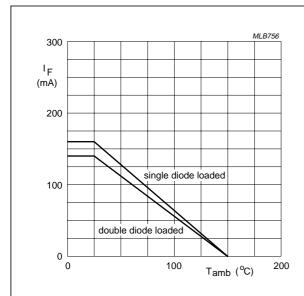
Note

1. Device mounted on a FR4 printed-circuit board.

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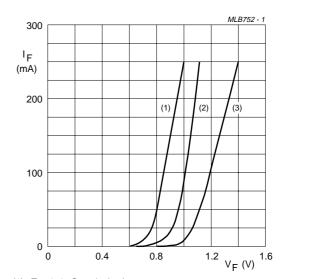
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GRAPHICAL DATA



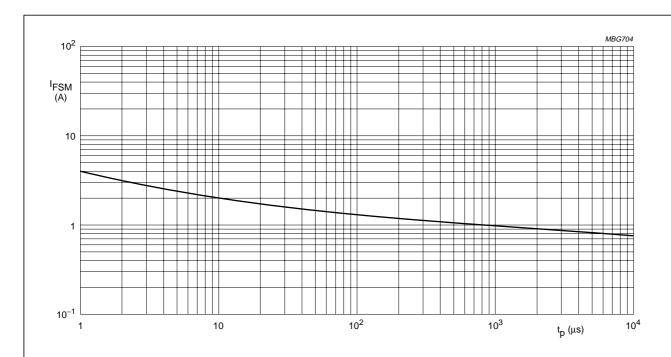
Device mounted on a FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.

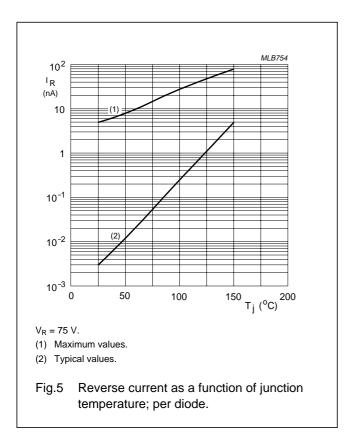


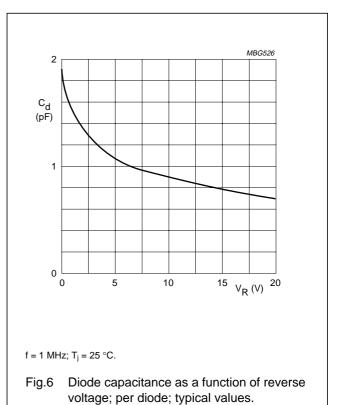
Based on square wave currents; $T_j = 25$ °C prior to surge.

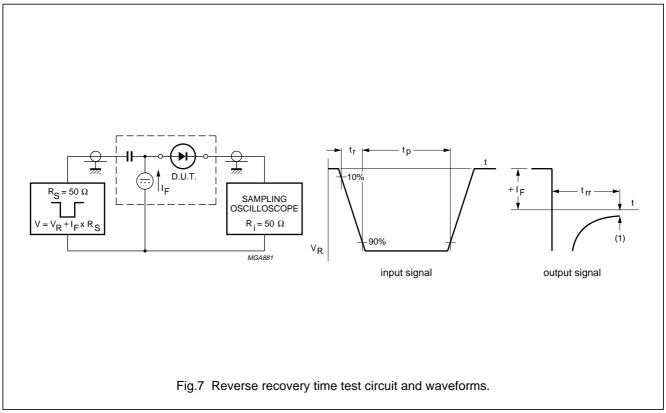
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

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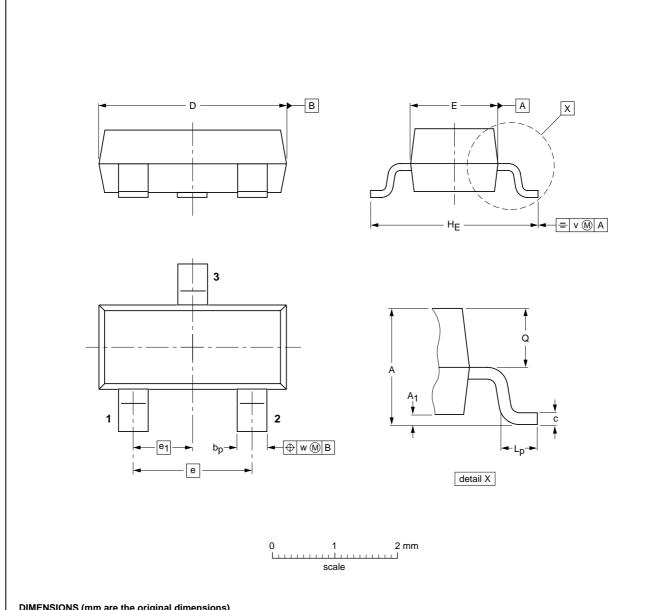
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | Α | A ₁ max. | bp | С | D | E | е | e ₁ | HE | L _p | Q | v | w |
|------|------------|------------------------|--------------|--------------|------------|------------|-----|----------------|------------|----------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|----------|-----------------------|------------|------------|-----------------------------------|
| VERSION | IEC | JEDEC | JEDEC EIAJ PROJECTION | | ISSUE DATE | |
| SOT23 | | TO-236AB | | | | -97-02-28- 99-09-13 |

2001 Oct 12 6

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DATA SHEET STATUS

| DATA SHEET STATUS(1) | PRODUCT STATUS ⁽²⁾ | DEFINITIONS |
|----------------------|----------------------------------|--|
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